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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	09/943134
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Ho, Tu-Tu

Sheet 1 of 3

Attorney Docket No: 1303.020US1

US PATENT DOCUMENTS

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Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1) Applicant's unique citation designation number (optional) 2) Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%;">Application Number</td> <td>09/943134</td> </tr> <tr> <td>Filing Date</td> <td>August 30, 2001</td> </tr> <tr> <td>First Named Inventor</td> <td>Forbes, Leonard</td> </tr> <tr> <td>Group Art Unit</td> <td>2818</td> </tr> <tr> <td>Examiner Name</td> <td>Ho, Tu-Tu</td> </tr> </table>		Application Number	09/943134	Filing Date	August 30, 2001	First Named Inventor	Forbes, Leonard	Group Art Unit	2818	Examiner Name	Ho, Tu-Tu
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FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			
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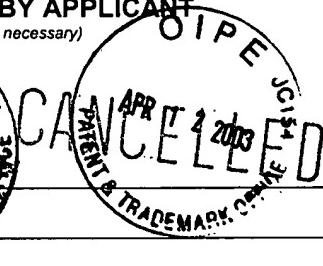
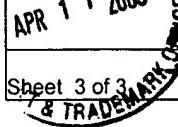
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Attorney Docket No: 1303.020US1

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